

Structural, optical and electrical characterization of Co-Pd doped TiO₂ semiconducting thin films sputtered on silicon

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Investigations of interface excitons at p-type GaAlAs/GaAs single heterojunctions in continuous wave and time resolved magneto photoluminescence experiments

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Optical and structural properties of sol-gel derived materials embedded in porous anodic alumina

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Circularly photostimulated electrogyration in europium- and terbium-doped GaN nanocrystals embedded in a silica xerogel matrix

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Photoreflectance investigations of a donor-related transition in AlGaIn/GaN transistor structures

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Photoluminescence from as-grown and annealed GaN_{0.027}As_{0.863}Sb_{0.11}/GaAs single quantum wells

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